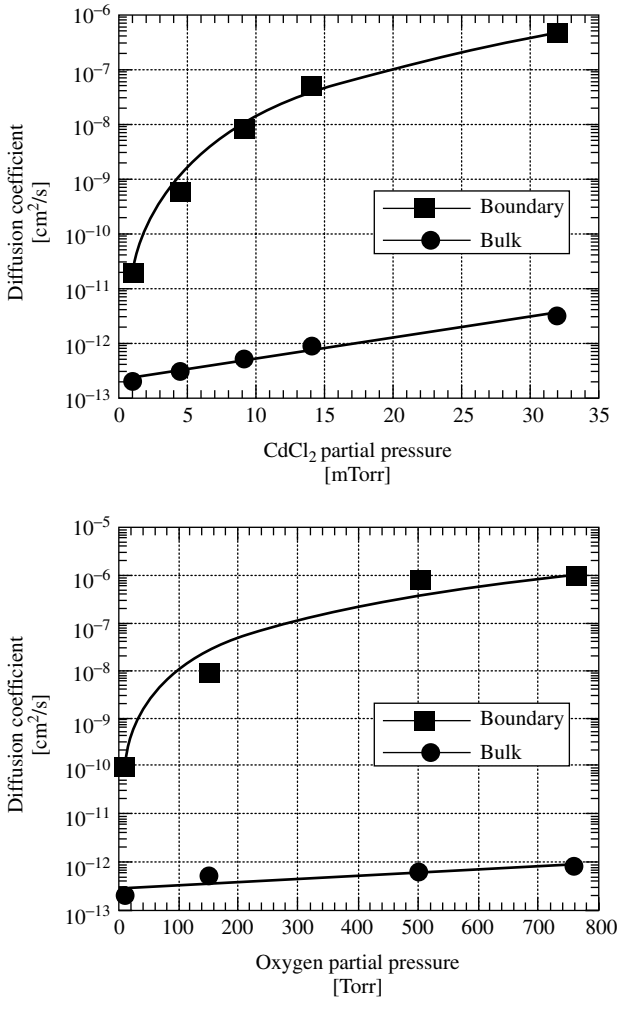

Figure 14.18 Sensitivity of bulk and grain-boundary diffusion coefficients (a) to $pCdCl_2$ at constant $pO_2 \sim 125$ Torr, at $T = 420^{\circ}C$, and (b) to pO_2 at constant $pCdCl_2 = 9$ mTorr, at $T = 420^{\circ}C$

from the differences in current generation, device operation is fundamentally similar for cells with differing amounts of $CdTe_{1-x}S_x$ alloy in the absorber layer.

14.3.4 Back Contact

The top region shown in Figure 14.7 is the back contact, consisting of a primary contact to CdTe, which typically consists of a tellurium-containing p^+ surface, and a secondary contact, which is the current-carrying conductor. As with other p-type semiconductors, there is a tendency to form a Schottky barrier with many metals, and achieving a low-resistance ohmic contact has proven to be challenging. The most common strategy is to form a Te-rich surface by selective chemical etching and then apply copper or a